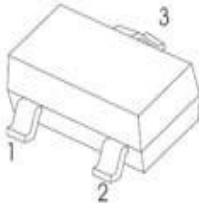
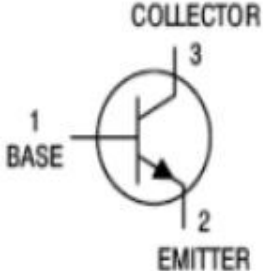


TRANSISTOR (NPN)	SOT-23 Plastic-Encapsulate Transistors		
<p><u>SOT-23</u></p>   <p>1.BASE 2.EMITTER 3.COLLECTOR</p> <p>Marking :1GM</p>	<p>Features</p> <ul style="list-style-type: none"> ※ Complimentary Type PNP Transistor MMBTA56 ※ For Switching and Amplifier Applications 		
MAXIMUM RATINGS (Ta=25°C unless otherwise noted)			
Parameter	Symbol	Value	Unit
Collector-Base Voltage	VCBO	80	V
Collector-Emitter Voltage	VCEO	80	V
Emitter-Base Voltage	VEBO	4	V
Collector Current	IC	500	mA
Collector Power Dissipation	PC	300	mW
Thermal Resistance From Junction To Ambient	RθJA	417	°C/W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55~+150	°C

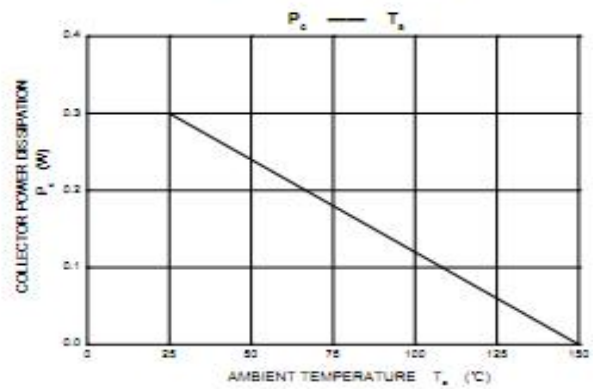
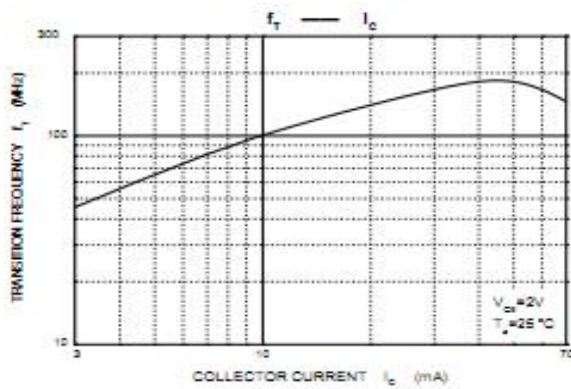
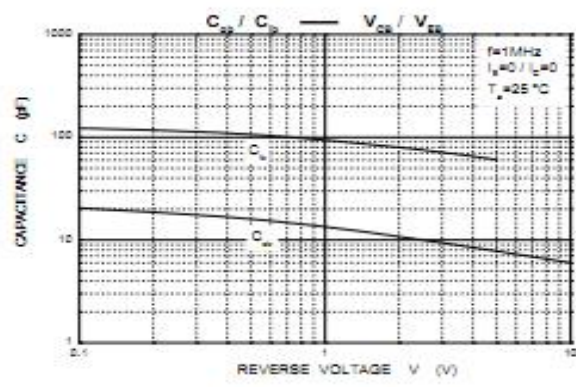
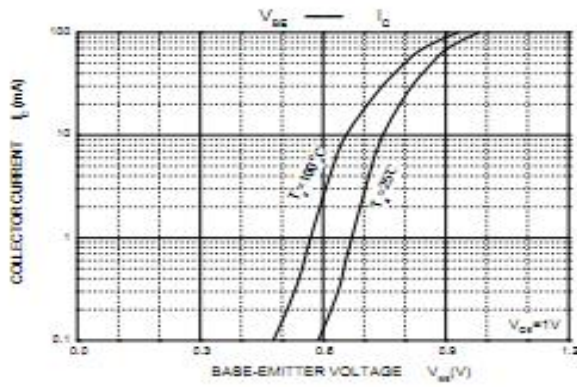
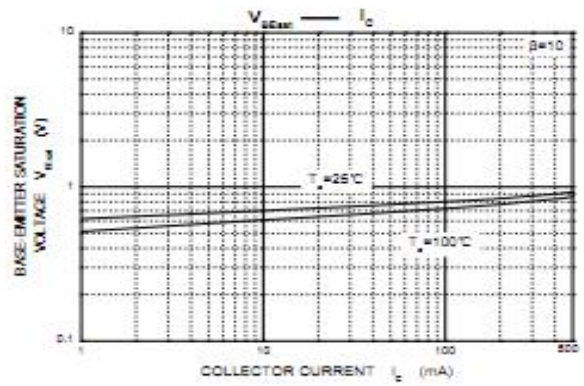
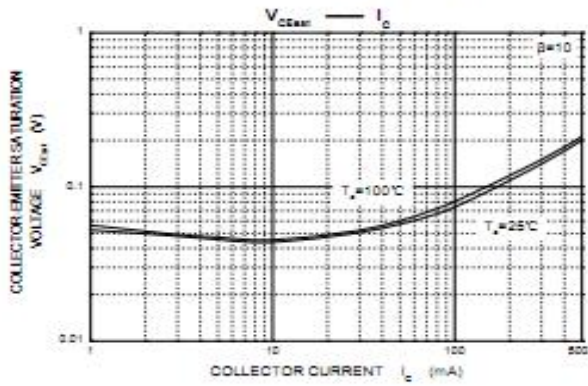
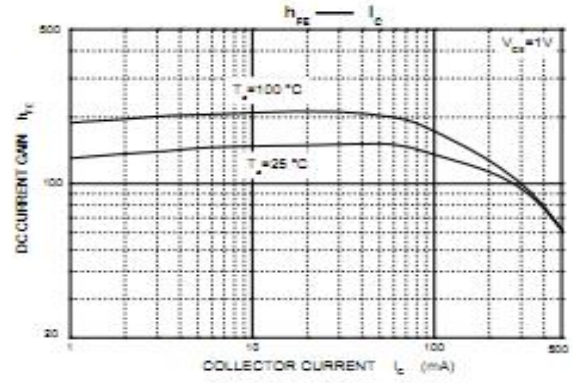
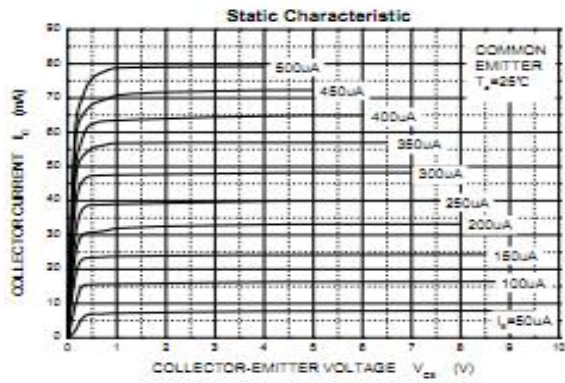
ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= 100 μA, IE=0	80			V
Collector-emitter breakdown voltage	V(BR)CEO	IC= 1mA, IB=0	80			V
Emitter-base breakdown voltage	V(BR)EBO	IE=100 μA, IC=0	4			V
Collector cut-off current	ICBO	VCB=80 V, IE=0			0.1	μA
Collector cut-off current	ICEO	VCB=60V, IE=0			1	μA
Emitter cut-off current	IEBO	VEB= 3V, IC=0			0.1	μA
DC current gain	hFE	VCE=1V, IC= 10mA	100		400	
	hFE	VCE=1V, IC= 100mA	100			
Collector-emitter saturation voltage	VCE(sat)	IC=100 mA, IB= 10mA			0.25	V
Base-emitter saturation voltage	VBE(sat)	IC=100 mA, IB= 10mA			1.2	V
Transition frequency	fT	VCE=2V, IC= 10mA f=100MHz	100			MHz

CLASSIFICATION OF hFI

Rank	L	H	
Range	80-120	120-250	

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)